

Supporting Information

Seed-Mediated Growth Synthesis and Tunable Narrow-band Luminescence of Quaternary Ag-In-Ga-S Alloyed Nanocrystals

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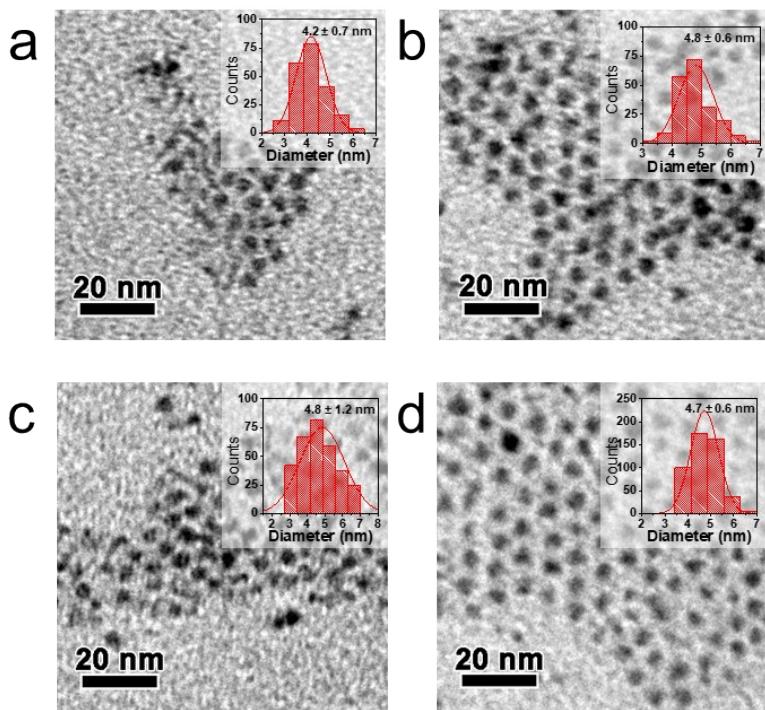


Fig. S1 TEM images of AIGS nanocrystals without DDT (a) 250°C, (b) 280°C 0 min, (c) 280°C 15 min, (d) 280°C 30 min.

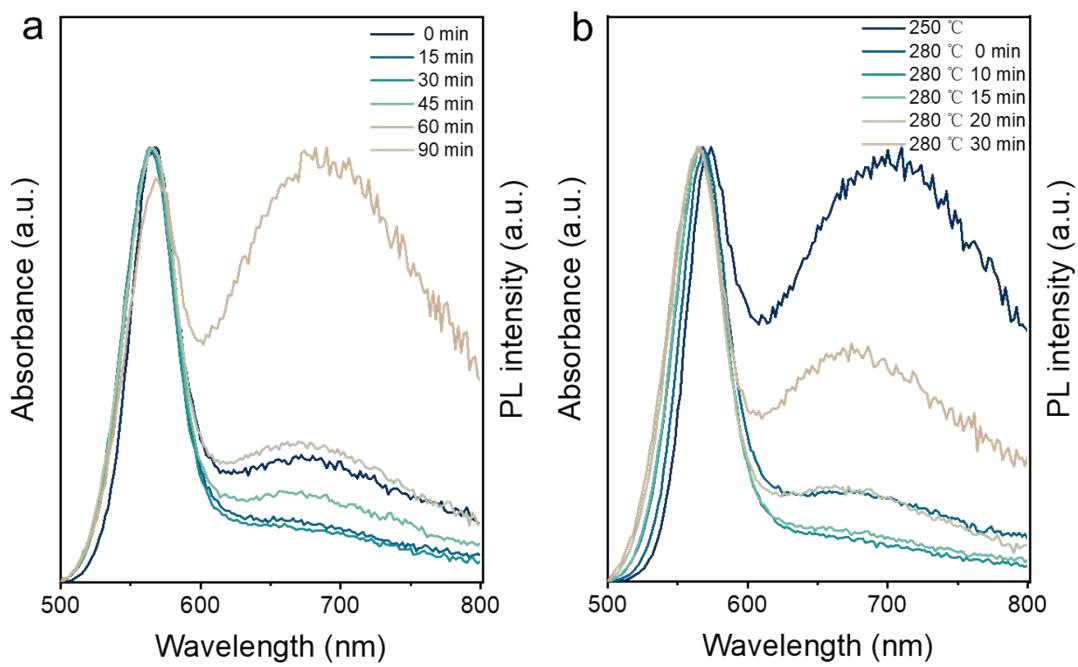


Fig. S2 Evolution of the PL spectra of AIGS nanocrystals with different Ga precursor (a) 0.3 mmol and (b) 0.5 mmol.

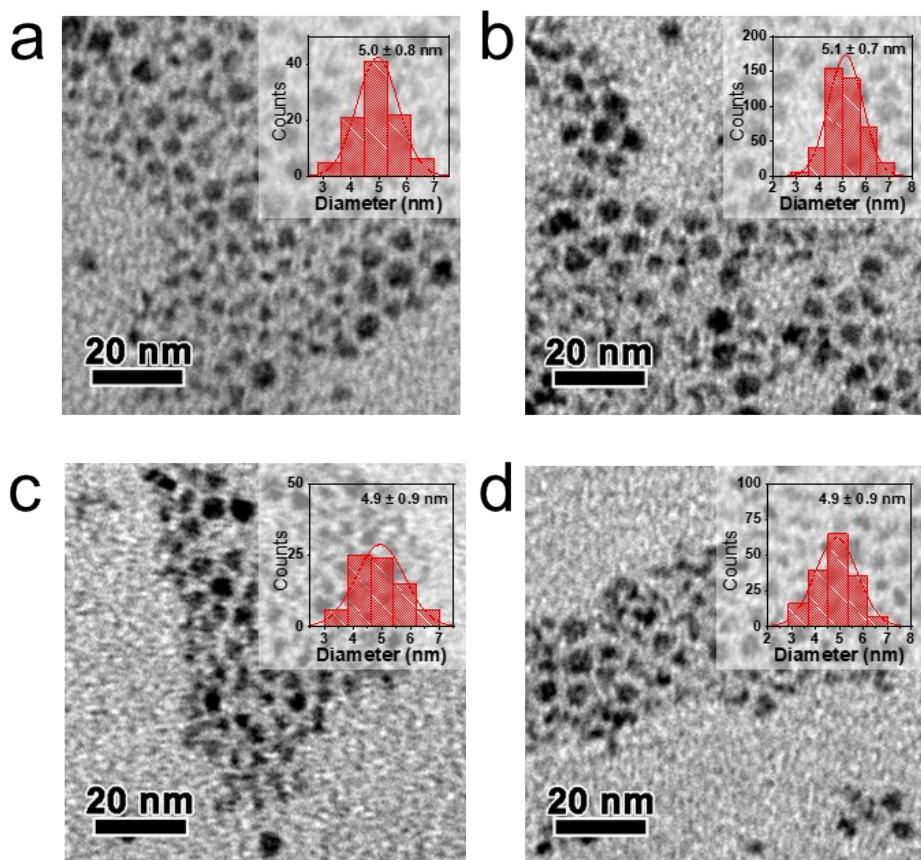


Fig. S3 TEM images of AIGS nanocrystals with DDT (a) 0 min, (b) 30 min, (c) 60 min, (d) 120 min.

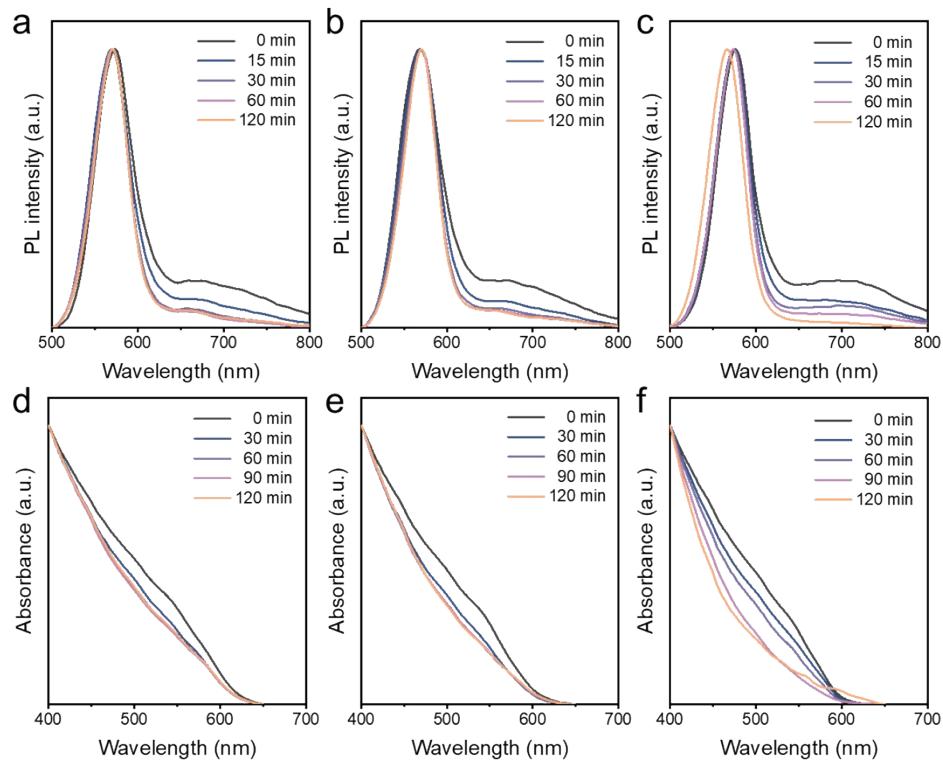


Fig. S4 Evolution of the PL spectra of AIGS nanocrystals with different addition of DDT (a) 0.1 mL, (b) 0.2 mL and (c) 0.5 mL.

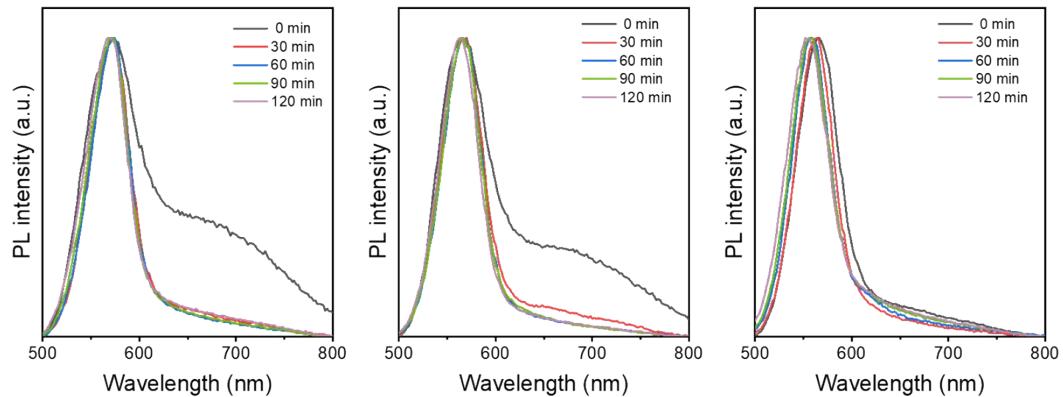


Fig. S5. Evolution of the PL spectra of AIGS nanocrystals with different addition of DMTU (a) 0.3 mmol, (b) 0.45 mmol and (c) 0.6 mmol.

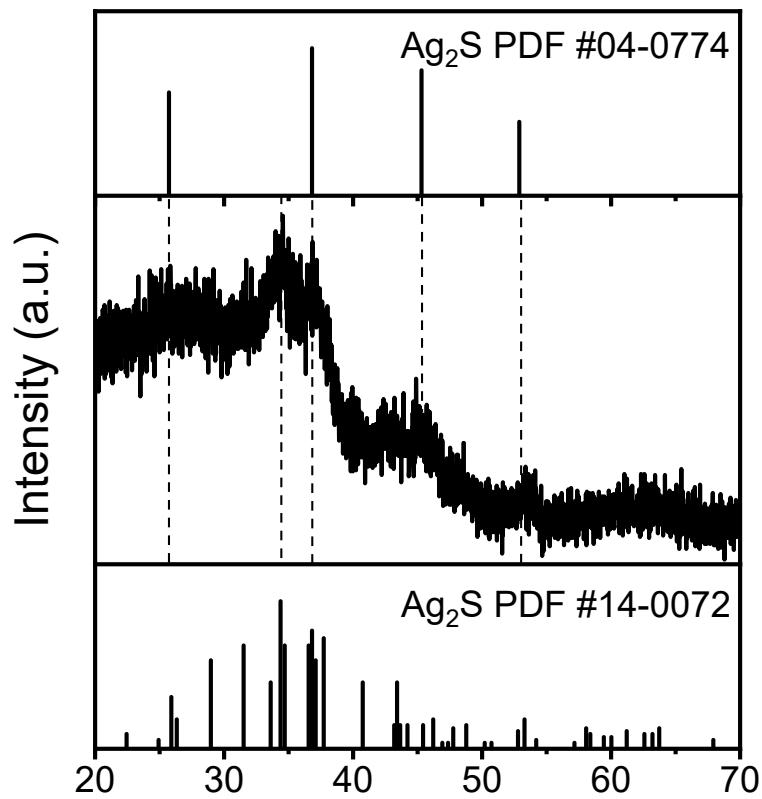


Fig. S6 XRD patterns of precipitate produced during the synthesis in AIS seeds.

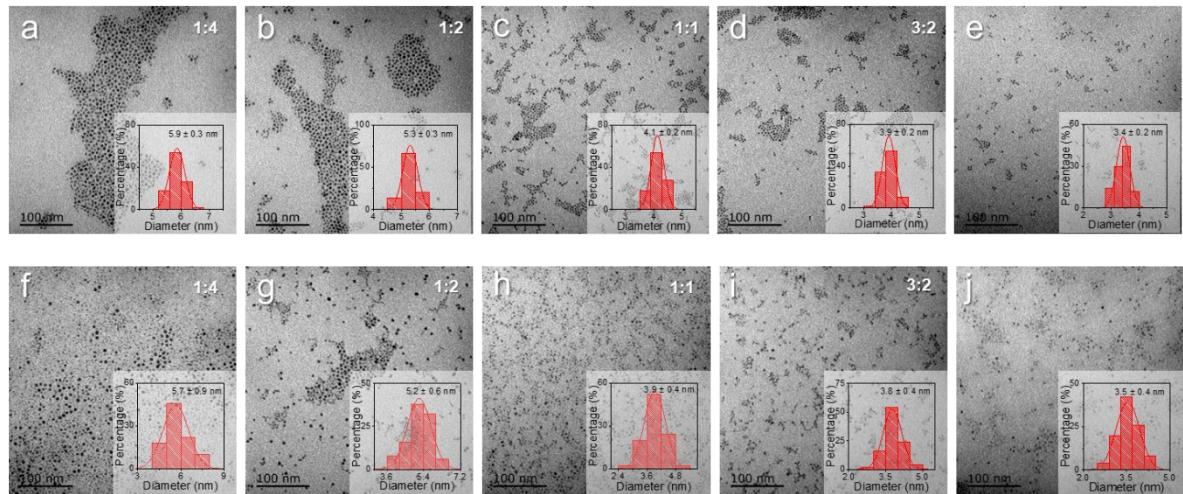


Fig. S7 TEM images of AIS seeds synthesized with different Ag/In (a) 1:4, (b) 1:2, (c) 1:1, (d) 3:2, (e) 2:1 and corresponding AIGS nanocrystals (f) 1:4, (g) 1:2, (h) 1:1, (i) 3:2, and (j) 2:1. The insets show the size distribution.

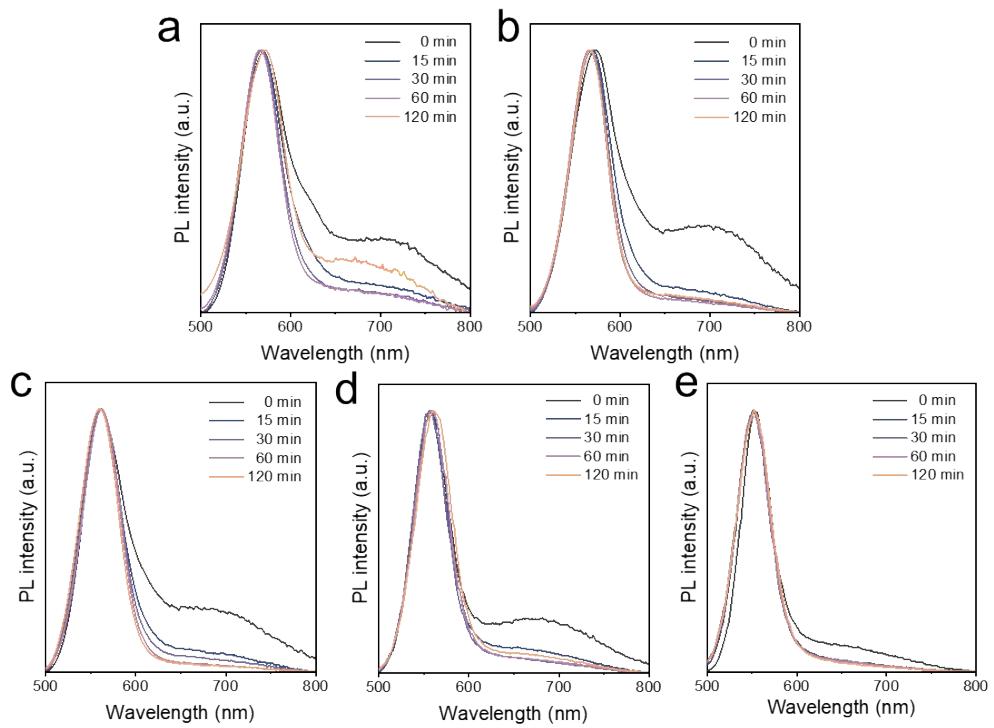


Fig. S8 PL spectra of AIGS nanocrystals with different Ag/In when AIS seeds synthesis (a) 1:4, (b) 1:2, (c) 1:1, (d) 3:2 and (e) 2:1.

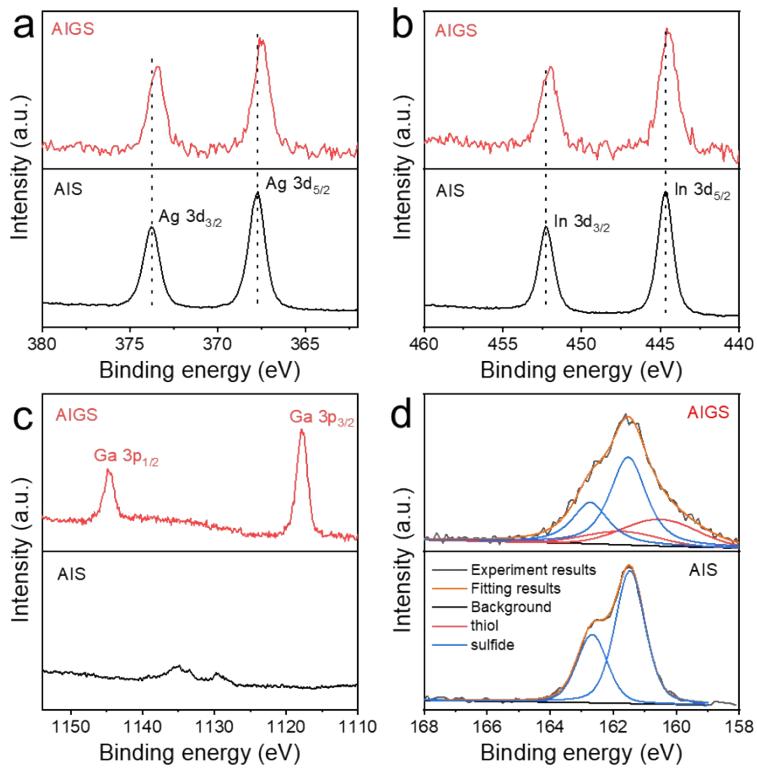


Fig. S9 XPS results of AIS seeds (Ag:In = 1:1) and corresponding AIGS nanocrystals (a) Ag 3d, (b) In 3d, (c) Ga 3p and (d) S.

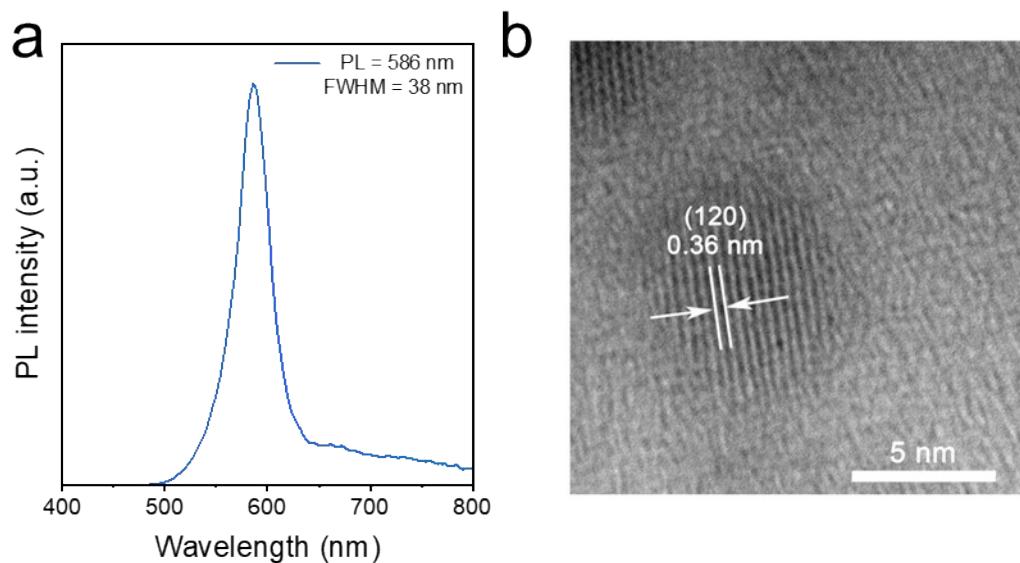


Fig. S10 (a) PL spectra and (b)HRTEM of large size (~ 8 nm) AIGS NCs were synthesized by using an equal amount of sulfur powder as a sulfur source.

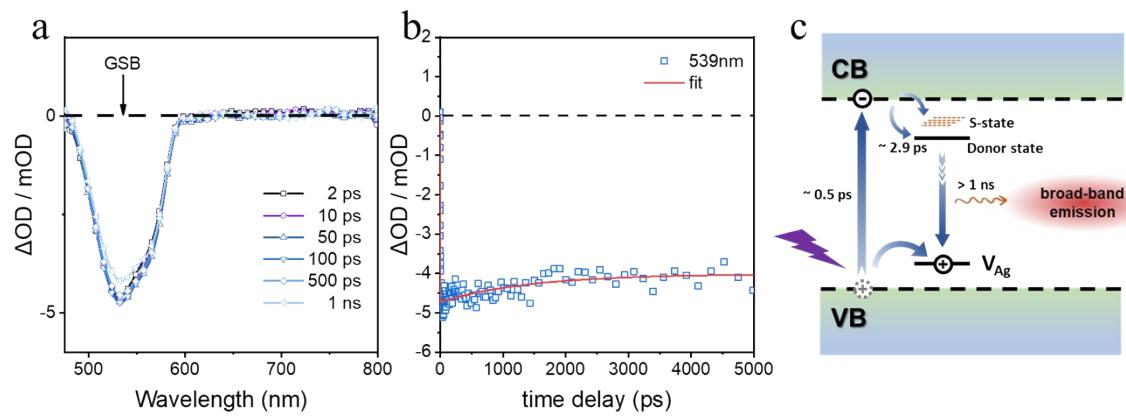


Fig. S11. (a) TA spectra of AIGS NCs excited by 365 nm pulses (b) TA kinetics of AIS NCs probed at the GSB (~ 539 nm) (c) Schematic illustration of the electron dynamics in AIS nanocrystals following bandgap excitation.

Table S1. PL decay components for AIGS NCs without 1-dodecanethiol

Sample	Reaction stage	τ_1/ns	α_1	τ_2/ns	α_2	τ_3/ns	α_3	$\tau_{\text{ave}}/\text{ns}$
Seeds (740 nm)	-	131.7	2.4%	690.7	42.5%	1548.0	55.1%	1149.8
Narrow-band luminescence peak (564 nm)	250°C	5.6	14.8%	31.9	22.0%	175.9	63.2%	119.0
	0 min	6.8	6.9%	34.0	29.8%	151.0	63.4%	106.3
	15 min	10.9	4.1%	46.4	39.7%	147.5	56.2%	101.7
	30 min	8.5	4.3%	38.0	33.8%	151.8	61.9%	107.1
Broad-band luminescence peak (670 nm)	250 °C	5.5	2.2%	37.1	7.0%	315.6	90.8%	289.3
	0 min	5.6	3.0%	36.9	9.3%	281.4	87.6%	250.1
	15 min	5.6	2.2%	37.6	10.9%	251.5	86.9%	222.6

Table S2. Element atomic ratio (ICP analysis) of AIGS NCs (without DDT during the AIGS NCs growth.)

Sample	Element	Seed	250°C	0min	15min	30min
AIGS NCs	Ag	38.7%	3.5%	4.4%	3.4%	4.5%
	Ga	-	91.0%	87.8%	88.5%	89.5%
	In	61.3%	5.5%	7.8%	8.1%	6.0%

Table S3. PL decay components for AIGS NCs with 1-dodecanethiol

Sample	Reaction stage	τ_1/ns	α_1	τ_2/ns	α_2	τ_3/ns	α_3	τ_{ave}/ns
Seeds (740 nm)	-	131.7	2.4%	690.7	42.5%	1548.0	55.1%	1149.8
Narrow-band emission peak (560 nm)	0 min	12.1	9.2%	46.1	32.2%	176.0	58.6%	119.0
	30 min	11.7	6.1%	47.7	39.8%	160.3	54.1%	106.5
	60 min	13.8	6.1%	48.7	41.0%	161.0	52.9%	105.9
	120 min	13.0	8.3%	48.8	42.1%	163.4	49.6%	102.7
Broad-band emission peak (670 nm)	0 min	5.3	2.7%	34.8	11.7%	249.1	85.6%	217.5
	30 min	5.2	3.2%	33.5	13.2%	234.8	83.5%	200.7
	60 min	5.1	3.9%	31.8	14.8%	226.9	81.3%	189.3
	120 min	5.1	3.2%	31.1	16.4%	209.4	80.4%	173.6

Table S4. Element atomic ratio (ICP analysis) of AIGS NCs (with DDT during the AIGS NCs growth.)

Sample	Element	Seed	0 min	30 min	60 min	120 min
AIGS NCs	Ag	38.7%	20.7%	16.8%	16.5%	15.1%
	Ga	-	55.3%	61.2%	63.8%	66.1%
	In	61.3%	24.0%	22.0%	19.6%	18.8%

Table S5. Element atomic ratio of AIS seeds synthesized with different Ag/In and corresponding AIGS NCs

Sample	Element	1:4	1:2	1:1	3:2	2:1
AIS seeds	Ag	46.7%	43.2%	38.7%	34.6%	29.6%
	In	53.3%	56.8%	61.3%	65.4%	70.4%
	Ag/In	0.88	0.76	0.63	0.52	0.42
AIGS NCs	Ag	9.5%	7.7%	5.5%	4.8%	3.4%
	Ga	78.9%	80.2%	83.5%	84.2%	88.5%
	In	11.6%	12.1%	11.0%	11.0%	8.1%
	Ag/In	0.82	0.64	0.5	0.43	0.42

Table S6. Stripping XPS element atomic ratio of AIGS NCs

Sample	Element	Step 0	Step 1	Step 2	Step 3
AIGS NCs	Ag	11.4%	13.7%	14.3%	14.8%
	In	10.8%	13.9%	14.7%	16.4%
	Ga	77.8%	72.4%	71.0%	68.7%

Table S7. Element atomic ratio (ICP analysis) of large-size AIGS NCs (size ~ 8 nm)

Sample	Element	Seed	AIGS
Large size AIGS NCs (size ~ 8 nm)	Ag	13.1%	11.9%
	Ga	-	46.2%
	In	86.9%	41.9%

Table S8. Kinetics fitting parameters for Fig. 5.

	τ_1/ns	τ_2/ns	τ_3/ns
GSB (524 nm)	0.9±0.4	53.2±3.7	-
SE (565 nm)	1.4±0.4	35.9±5.2	270±77

Table S9. Kinetics fitting parameters for Fig. S11.

	τ_1/ps	τ_2/ps	τ_3/ps
GSB (539 nm)	0.5 ± 0.2	2.9 ± 26	1412 ± 921